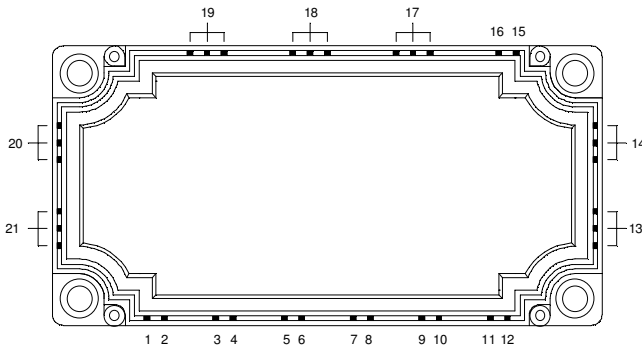
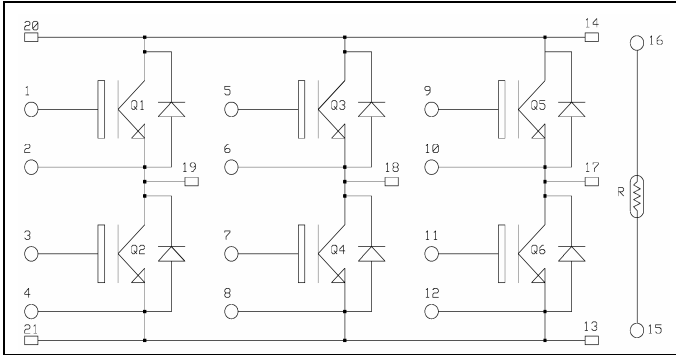


## 3 Phase bridge NPT IGBT Power Module

$V_{CES} = 1700V$   
 $I_C = 75A @ T_c = 80^\circ C$



### Application

- AC Motor control

### Features


- Non Punch Through (NPT) Low Loss IGBT®
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

### Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1700	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	150
		$T_C = 80^\circ C$	75
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	250
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	625
RBSOA	Reverse Bias Operating Area	$T_j = 125^\circ C$	150A@1600V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## Electrical Characteristics

All ratings @ T<sub>j</sub> = 25°C unless otherwise specified

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV <sub>CES</sub>	Collector - Emitter Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA	1700			V
I <sub>CES</sub>	Zero Gate Voltage Collector Current	V <sub>GE</sub> = 0V V <sub>CE</sub> = 1700V		0.03 2	0.15	mA
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C				
V <sub>CE(on)</sub>	Collector Emitter on Voltage	V <sub>GE</sub> = 15V I <sub>C</sub> = 75A		2.7 3.2	3.3	V
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C				
V <sub>GE(th)</sub>	Gate Threshold Voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 3.5 mA	4.5		6.5	V
I <sub>GES</sub>	Gate - Emitter Leakage Current	V <sub>GE</sub> = 20V, V <sub>CE</sub> = 0V			100	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C <sub>ies</sub>	Input Capacitance	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 25V f = 1MHz		5000		pF
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C) V <sub>GE</sub> = ±15V V <sub>Bus</sub> = 900V I <sub>C</sub> = 75A R <sub>G</sub> = 20Ω		100		ns
T <sub>r</sub>	Rise Time			100		
T <sub>d(off)</sub>	Turn-off Delay Time			800		
T <sub>f</sub>	Fall Time			30		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C) V <sub>GE</sub> = ±15V V <sub>Bus</sub> = 900V I <sub>C</sub> = 75A R <sub>G</sub> = 20Ω		100		ns
T <sub>r</sub>	Rise Time			100		
T <sub>d(off)</sub>	Turn-off Delay Time			900		
T <sub>f</sub>	Fall Time			30		
E <sub>off</sub>	Turn off Energy				22	

## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 75A V <sub>GE</sub> = 0V		2.2 2.0	2.6	V
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C				
E <sub>r</sub>	Reverse Recovery Energy	I <sub>F</sub> = 75A V <sub>R</sub> = 900V di/dt = 900A/μs		3.5 6.5		mJ
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C				
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 75A V <sub>R</sub> = 900V di/dt = 900A/μs		9 19		μC
		T <sub>j</sub> = 25°C T <sub>j</sub> = 125°C				

## Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		5		kΩ
B <sub>25/50</sub>	T <sub>25</sub> = 298.16 K		3375		K

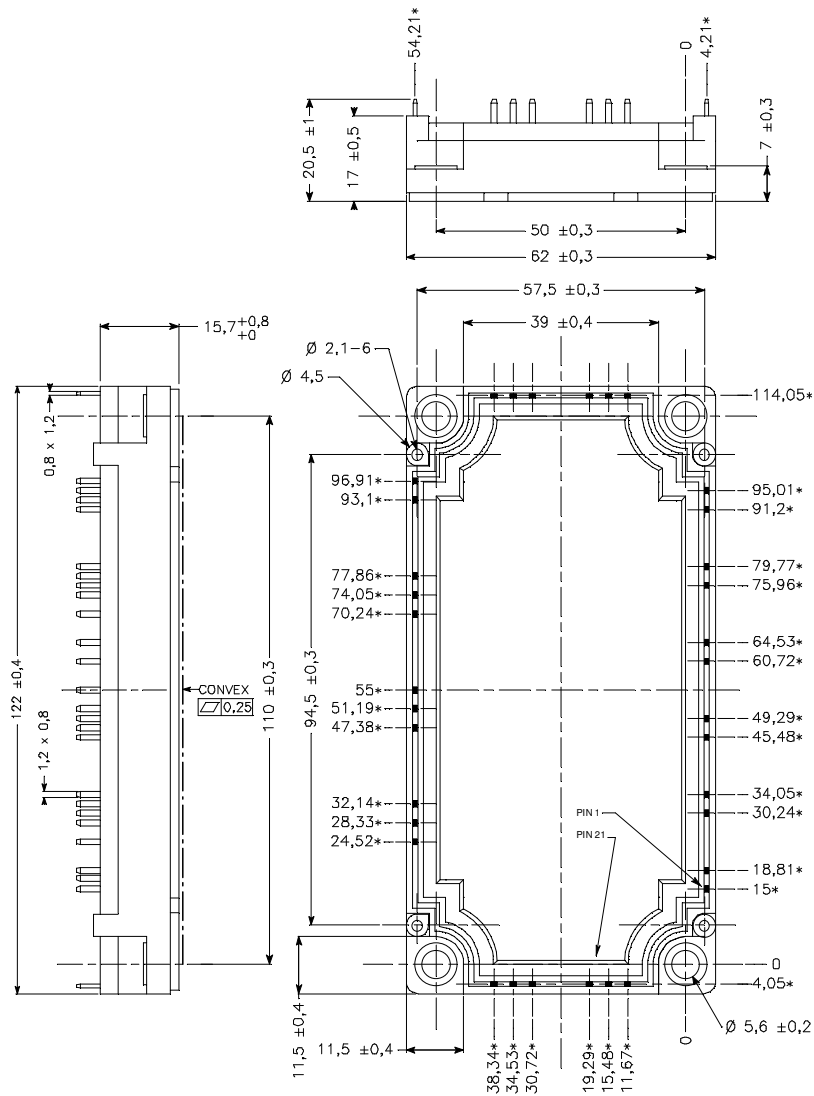
$$R_T = \frac{R_{25}}{\exp\left[B_{25/50} \left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case	IGBT		0.2	°C/W	
		Diode		0.47		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		125		
Torque	Mounting torque	To Heatsink	M5	3	4.5	N.m
Wt	Package Weight				300	g

**Package outline**



ALL DIMENSIONS MARKED \*\*\* ARE TOLERANCED AS:  $\pm 0.2$

**APT reserves the right to change, without notice, the specifications and information contained herein**

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.